

I claim:

1. A method of CMP comprising:  
forming a CMP slurry containing cerium oxide;  
adding a slurry modifier to the slurry, wherein the slurry  
5 modifier polishes low structure areas at a substantially zero rate and  
polishes high structure areas at a rate approximating a blanket polishing  
rate; and  
polishing a structure using the modifier-contained slurry.
2. The method of claim 1 wherein said forming includes setting  
a cerium oxide concentration of between about 1% and 50% by weight.
3. The method of claim 1 wherein said polishing includes CMP  
at a pressure of between about five psi and ten psi.
4. The method of claim 1 wherein said adding includes adding  
ethylene glycol at a concentration of up to 50%.
5. A method of CMP comprising:  
forming a CMP slurry containing cerium oxide at a  
concentration of between about 1% and 50% by weight;  
adding a slurry modifier to the slurry, wherein the slurry  
5 modifier polishes low structure areas at a substantially zero rate and  
polishes high structure areas at a rate approximating a blanket polishing  
rate; and  
polishing a structure using the modifier-contained slurry.

6. The method of claim 5 wherein said polishing includes CMP at a pressure of between about five psi and ten psi.

7. The method of claim 5 wherein said adding includes adding ethylene glycol at a concentration of up to 50%.

8. A method of CMP comprising:

forming a CMP slurry containing cerium oxide at a concentration of between about 1% and 50% by weight;

5 adding ethylene glycol at a concentration of up to 50% for polishing low structure areas at a substantially zero rate and polishing high structure areas at a rate approximating a blanket polishing rate; and polishing a structure using the slurry.

9. The method of claim 8 wherein said polishing includes CMP at a pressure of between about five psi and ten psi.